

EPITAXX

*InGaAs Planar PIN Photodiode/GaAs FET
Hybrid Receiver Module*

DESCRIPTION

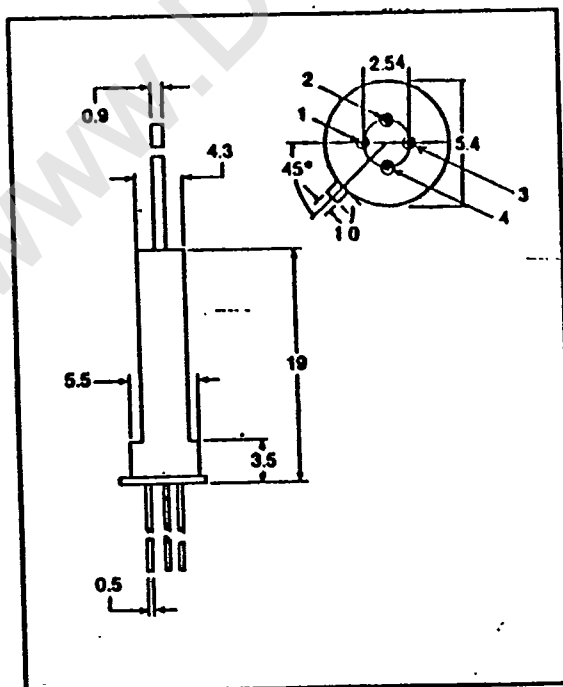
The ERM 7501FJ is a hybrid device containing a high speed InGaAs planar PIN photodiode and GaAs FET in a hermetically sealed package with integral fiber pigtail. It is designed for local optical communication and long haul telecommunication applications.

FEATURES

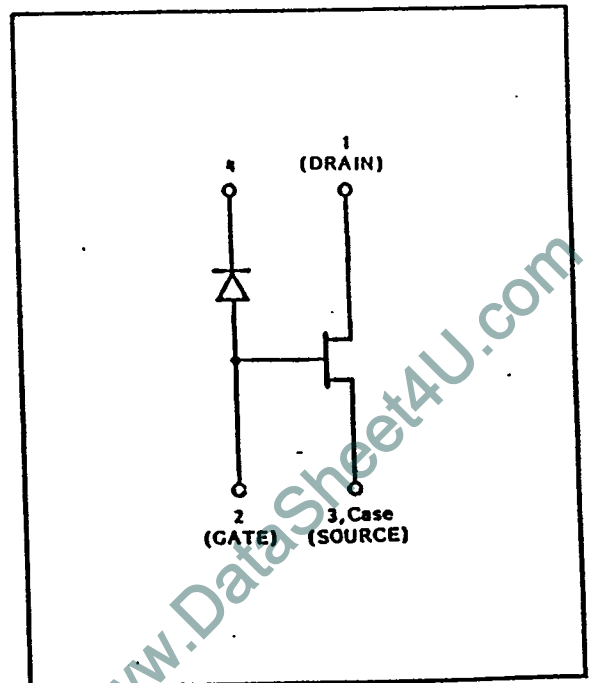
- Low dark current, high reliability InGaAs photodiode.
- High speed, low noise GaAs FET
- User selected gain/bandwidth
- Hermetically sealed fiber pigtail package
- Optional fiber types and connectorization

DIMENSIONS

ERM 7501FJ



DIMENSIONS IN MM



SPECIFICATIONSAt T = 25C and V_R = 5V unless otherwise indicated.

Parameter	ERM 7501FJ			Unit
	Min.	Typ.	Max.	
Detector Active Diameter		75		um
Spectral Response	0.8		1.7	um
Responsivity @ 1300nm	0.65	0.80		A/W
Dark Current		0.5	3.0	nA
Capacitance		1.5	3.0	pF
FET Transconductance V _{ds} =3V, I _{ds} =10mA	35	40		mS

MAXIMUM RATINGS

Parameter		ERM 7501FJ	Unit
PIN Photodiode	Reverse Voltage	25	V
	Reverse Current	10	mA
	Forward Current	0.5	mA
FET	Drain-Source Voltage	6	V
	Gate-Source Voltage	-5	V
	Drain Current	75	mA
	Power Dissipation	200	mW
Operating Temperature		85	C
Storage Temperature		125	C

OPTIONS

- ERM 7501FJ/FC-62.5
Multimode (62.5/125)
- ERM 7501FJ/FC-SM
Singlemode (9/125) 0/140)

- ERM 7501FC with connector

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